

COLLEGE OF ENGINEERING AND TECHNOLOGIES ALMUSTAQBAL UNIVERSITY

Electronics CTE 207

Lecture 15

- Bipolar Junction Transistors (BJT) II -(2023 - 2024) Dr. Zaidoon AL-Shammari Lecturer / Researcher

zaidoon.waleed@mustaqbal-college.edu.iq

www.uomus.edu.iq



- The transistor is a three-layer semiconductor device consisting of either two n- and one p-type layers of material or two p- and one n-type layers of material.
- The former is called an npn transistor, while the latter is called a pnp transistor.
- In Fig. below both biasing potentials have been applied to a pnp transistor, with the resulting majority- and minority-carrier flow indicated.



The most frequently encountered transistor configuration appears in Figure below for the pnp and npn transistors.

It is called the common emitter configuration since the emitter is common or reference to both the input and output terminals (in this case common to both the base and collector terminals).

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For the common-emitter configuration, the output characteristics are a plot of the output current (IC) versus output voltage (VCE) for a range of values of input current (IB).

➤ The input characteristics are a plot of the input current (IB) versus the input voltage (VBE) for a range of values of output voltage (VCE).



Ic (mA) 8 90 μA 80 μA 7 70 µA $I_B(\mu A)$ $V_{CE} = 1 \text{ V}$ $V_{CE} = 10 \text{ V}$ 6 60 µA 100 50 µA $V_{CE} = 20 \text{ V}$ (Saturation region) 5 90 40 µA 80 4 70 30 µA 60 -3 (Active region) 50 20 µA 40 2 30 10 µA 20 10 $I_B = 0 \,\mu A$ $20 \quad V_{CE} (V)$ 0 10 15 0.6 0.8 5 0 0.2 0.4 1.0 VBE (V) V_{CEsat} (Cutoff region) $I_{CEO} \cong \beta I_{CBO}$



In the dc mode the levels of I_C and I_B are related by a quantity called beta and defined by the following equation:

$$\beta_{dc} = \frac{I_C}{I_B}$$

For practical devices the level of typically ranges from about 50 to over 400, with most in the midrange.

A relationship can be developed between β and α using the basic relationships introduced thus far. Using $\beta = I_C/I_B$ we have $I_B = I_C/\beta$, and from $\alpha = I_C/I_E$ we have

Example







$$\beta_{\rm ac} = \frac{\Delta I_C}{\Delta I_B} \Big|_{V_{CE=\rm constant}}$$

$$\beta_{ac} = \frac{\Delta I_C}{\Delta I_B} \Big|_{V_{CE=constant}} = \frac{I_{C_2} - I_{C_1}}{I_{B_2} - I_{B_1}}$$
$$= \frac{3.2 \text{ mA} - 2.2 \text{ mA}}{30 \,\mu\text{A} - 20 \,\mu\text{A}} = \frac{1 \text{ mA}}{10 \,\mu\text{A}}$$
$$= 100$$

$$\beta_{\rm dc} = \frac{I_C}{I_B} = \frac{2.7 \text{ mA}}{25 \ \mu \text{A}} = 108$$

Dr. Zaidoon AL-Shammari

Example



Determining β_{ac} and β_{dc} from the collector characteristics.



 $I_E = I_C / \alpha$. Substituting into

we have
$$\frac{I_C}{\alpha} = I_C + \frac{I_C}{\beta}$$

and dividing both sides of the equation by I_C will result in

 $I_E = I_C + I_B$

or
so that
$$\frac{1}{\alpha} = 1 + \frac{1}{\beta}$$

$$\beta = \alpha\beta + \alpha = (\beta + 1)\alpha$$

$$\alpha = \frac{\beta}{\beta + 1}$$
or
$$\beta = \frac{\alpha}{1 - \alpha}$$

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The common-collector configuration is used primarily for impedancematching purposes since it has a high input impedance and low output impedance, opposite to that of the common-base and common-emitter configurations.



- For all practical purposes, the output characteristics of the common collector configuration are the same as for the common-emitter configuration.
- For the common-collector configuration the output characteristics are a plot of IE versus VCE for a range of values of IB.
- The input current, therefore, is the same for both the common-emitter and common-collector characteristics.

Common-Collector Configuration

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 V_{EE}





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